

5 MHz, 0.5 mA, Zero-Drift Op Amps

Features

- High DC Precision:
 - V_{OS} Drift: ±20 nV/°C (maximum, V_{DD} = 5.5V)
 - V_{OS}: ±9 μV (maximum)
 - A_{OL}: 126 dB (minimum, V_{DD} = 5.5V)
 - PSRR: 117 dB (minimum, V_{DD} = 5.5V)
 - CMRR: 118 dB (minimum, V_{DD} = 5.5V)
 - E_{ni} : 0.28 μV_{P-P} (typical), f = 0.1 Hz to 10 Hz
 - E_{ni} : 0.1 μV_{P-P} (typical), f = 0.01 Hz to 1 Hz
- Enhanced EMI Protection:
- Electromagnetic Interference Rejection Ratio (EMIRR) at 1.8 GHz: 101 dB
- Low Power and Supply Voltages:
 - I_Q: 0.5 mA/amplifier (typical)
 - Wide supply voltage range: 2.2V to 5.5V
- Small Packages:
 - Singles in SC70, SOT-23
 - Duals in MSOP-8, 2x3 TDFN
 - Quads in TSSOP-14
- · Easy to Use:
 - Rail-to-rail input/output
 - Gain Bandwidth Product: 5 MHz (typical)
 - Unity Gain Stable
- Extended Temperature Range: -40°C to +125°C

Typical Applications

- Portable Instrumentation
- Sensor Conditioning
- Temperature Measurement
- DC Offset Correction
- Medical Instrumentation

Design Aids

- · SPICE Macro Models
- FilterLab[®] Software
- Microchip Advanced Part Selector (MAPS)
- · Analog Demonstration and Evaluation Boards
- Application Notes

Related Parts

- MCP6V11/1U/2/4: Zero-Drift, Low Power
- MCP6V31/1U/2/4: Zero-Drift, Low Power
- MCP6V61/1U/2/4: Zero-Drift, 1 MHz
- MCP6V71/1U/2/4: Zero-Drift, 2 MHz
- MCP6V91/1U/2/4: Zero-Drift, 10 MHz

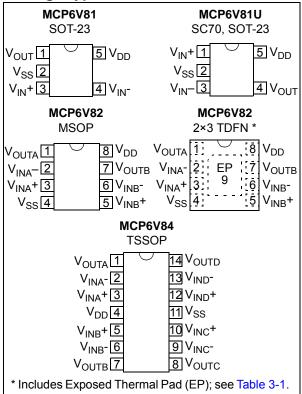
Description

The Microchip Technology Incorporated MCP6V81/1U/2/4 family of operational amplifiers provides input offset voltage correction for very low offset and offset drift. These devices have a gain bandwidth product of 5 MHz (typical). They are unity-gain stable, have virtually no 1/f noise and have good Power Supply Rejection Ratio (PSRR) and Common Mode Rejection Ratio (CMRR). These products operate with a single supply voltage as low as 2.2V, while drawing 500 µA/amplifier (typical) of quiescent current.

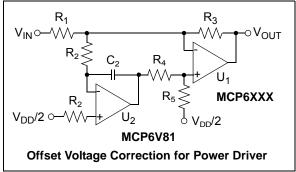
The MCP6V81/1U/2/4 family has enhanced EMI protection to minimize any electromagnetic interference from external sources. This feature makes it well suited for EMI-sensitive applications such as power lines, radio stations and mobile communications, etc.

The MCP6V81/1U/2/4 op amps are offered in single (MCP6V81 and MCP6V81U), dual (MCP6V82) and quad (MCP6V84) packages. They were designed using an advanced CMOS process.

Package Types



Typical Application Circuit



Figures 1 and 2 show the input offset voltage of the single-channel device MCP6V81/1U versus the ambient temperature for different power supply voltages.

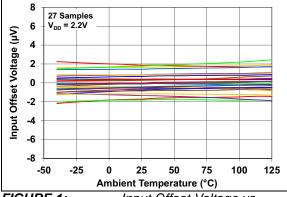


FIGURE 1: Input Offset Voltage vs. Ambient Temperature with $V_{DD} = 2.2V$.

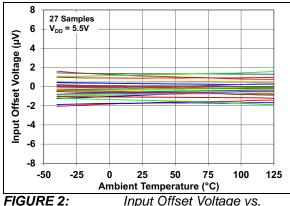


FIGURE 2: Input Offset Voltage vs. Ambient Temperature with $V_{DD} = 5.5V$.

As seen in Figures 1 and 2, the MCP6V81/1U op amps have excellent performance across temperature. The input offset voltage temperature drift (TC₁) shown is well within the specified maximum values of 20 nV/°C at V_{DD} = 5.5V and 25 nV/°C at V_{DD} = 2.2V.

This performance supports applications with stringent DC precision requirements. In many cases, it will not be necessary to correct for temperature effects (i.e., calibrate) in a design. In the other cases, the correction will be small.

1.0 ELECTRICAL CHARACTERISTICS

1.1 Absolute Maximum Ratings †

V _{DD} – V _{SS}	6.5V
Current at Input Pins	±2 mA
Analog Inputs (V _{IN} + and V _{IN} -) ⁽¹⁾	$V_{SS} - 1.0V$ to $V_{DD} + 1.0V$
All Other Inputs and Outputs	\dots V _{SS} – 0.3V to V _{DD} + 0.3V
Difference Input Voltage	V _{DD} – V _{SS}
Output Short Circuit Current	Continuous
Current at Output and Supply Pins	±30 mA
Storage Temperature	65°C to +150°C
Maximum Junction Temperature	+150°C
ESD protection on all pins (HBM, CDM, MM)	
MCP6V81/1U	≥4 kV, 1.5 kV, 400V
MCP6V82/4	\geq 4 kV, 1.5 kV, 300V

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Note 1: See Section 4.2.1 "Rail-to-Rail Inputs".

1.2 Specifications

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to $+5.5V$, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$ (refer to Figures 1-4 and 1-5).									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Input Offset									
Input Offset Voltage	V _{OS}	-9	—	+9	μV	T _A = +25°C			
Input Offset Voltage Drift with Temperature (Linear Temperature Coefficient)	TC₁	-25	_	+25	nV/°C	T _A = -40 to +125°C, V _{DD} = 2.2V (Note 1)			
		-20	_	+20	nV/°C	T _A = -40 to +125°C, V _{DD} = 5.5V (Note 1)			
Input Offset Voltage Quadratic Temperature Coefficient	TC ₂	—	±30	-	pV/°C ²	T _A = -40 to +125°C V _{DD} = 2.2V			
	102	_	±20	_	pV/°C ²	T _A = -40 to +125°C V _{DD} = 5.5V			
Input Offset Voltage Aging	ΔV_{OS}	_	±0.25	_	μV	408 hours Life Test at +150°, measured at +25°C.			
Power Supply Rejection Ratio	PSRR	117	127	—	dB				

Note 1: For design guidance only; not tested.

2: Figure 2-19 shows how V_{CML} and V_{CMH} changed across temperature for the first production lot.

Electrical Characteristics: Unless otherw $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$,	vise indi R ₁ = 10	cated, T _A =	= +25°C, V _{DD} and C ₄ = 30 n	$_{0} = +2.2V$ to	+5.5V, V	_{SS} = GND, 4 and 1-5)
Parameters	Sym.	Min.	тур.	Max.	Units	Conditions
Input Bias Current and Impedance						
Input Bias Current	I _B	-50	±2	+50	pА	
Input Bias Current across Temperature	Ι _Β	_	+10	<u> </u>	pА	T _A = +85°C
	I _B	0	+0.24	+1	nA	T _A = +125°C
Input Offset Current	I _{OS}	-400	±100	+400	pА	
Input Offset Current across Temperature	I _{OS}	_	±75	_	pА	T _A = +85°C
	I _{OS}	-500	±100	+500	рА	$T_{A} = +125^{\circ}C$
Common-mode Input Impedance	Z _{CM}	_	10 ¹³ 14	_	Ω pF	
Differential Input Impedance	Z _{DIFF}	_	10 ¹³ 3	_	Ω pF	
Common Mode	-					
Common-mode Input Voltage Range Low	V _{CML}			V _{SS} -0.2	V	Note 2
Common-mode Input Voltage Range High	V _{CMH}	V _{DD} +0. 3		—	V	Note 2
Common-mode Rejection Ratio	CMR R	112	128	—	dB	V _{DD} = 2.2V, V _{CM} = -0.2V to 2.5V (Note 2)
	CMR R	118	136	—	dB	V _{DD} = 5.5V, V _{CM} = -0.2V to 5.8V (Note 2)
Open-Loop Gain						
DC Open-Loop Gain (Large Signal)	A _{OL}	119	146	—	dB	V _{DD} = 2.2V, V _{OUT} = 0.3V to 2.0V
	A _{OL}	126	151	—	dB	V _{DD} = 5.5V, V _{OUT} = 0.3V to 5.3V
Output						
Minimum Output Voltage Swing	V _{OL}	V _{SS}	V _{SS} +35	V _{SS} +120	mV	$R_L = 1 k\Omega, G = +2,$ 0.5V input overdrive
	V _{OL}		V _{SS} +5		mV	$R_L = 10 \text{ k}\Omega, \text{ G} = +2,$ 0.5V input overdrive
Maximum Output Voltage Swing	V _{OH}	V _{DD} - 120	V _{DD} -45	V _{DD}	mV	$R_L = 1 k\Omega, G = +2,$ 0.5V input overdrive
	V _{OH}	—	V _{DD} –5	—	mV	$R_L = 10 \text{ k}\Omega, \text{ G} = +2,$ 0.5V input overdrive
Output Short-Circuit Current	I _{SC}	_	±15	—	mA	V _{DD} = 2.2V
	I _{SC}	_	±40	—	mA	V _{DD} = 5.5V
Power Supply						
Supply Voltage	V _{DD}	2.2		5.5	V	
	t .					

 V_{POR} Note 1: For design guidance only; not tested.

Quiescent Current per Amplifier

Power-on Reset (POR) Trip Voltage

2: Figure 2-19 shows how V_{CML} and V_{CMH} changed across temperature for the first production lot.

250

1.2

lQ

500

1.6

770

1.9

μA

V

 $I_{\rm O} = 0$

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to +5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$ (refer to Figures 1-4 and 1-5).							
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions	
Amplifier AC Response							
Gain Bandwidth Product	GBWP	_	5		MHz		
Slew Rate	SR	_	4	—	V/µs		
Phase Margin	PM		60	_	°C	G = +1	
Amplifier Noise Response							
Input Noise Voltage	E _{ni}		0.1	_	μV_{P-P}	f = 0.01 Hz to 1 Hz	
	E _{ni}		0.28	—	μV_{P-P}	f = 0.1 Hz to 10 Hz	
Input Noise Voltage Density	e _{ni}	_	13	—	nV/√Hz	f < 2 kHz	
Input Noise Current Density	i _{ni}		6	_	fA/√Hz		
Amplifier Distortion ⁽¹⁾							
Intermodulation Distortion (AC)	IMD		100	—	μV _{PK}	V_{CM} tone = 100 mV _{PK} at 1 kHz, G _N = 11, RTI	
Amplifier Step Response							
Start-Up Time	t _{STR}	_	100	-	μs	G = +1, 0.1% V _{OUT} settling (Note 2)	
Offset Correction Settling Time	t _{STL}		30	—	μs	G = +1, V _{IN} step of 2V, V _{OS} within 100 μ V of its final value	
Output Overdrive Recovery Time	t _{ODR}	_	60	_	μs	G = -10, ± 0.5 V input overdrive to V _{DD} /2, V _{IN} 50% point to V _{OUT} 90% point (Note 3)	
EMI Protection							
EMI Rejection Ratio	EMIRR	_	90	-	dB	V _{IN} = 0.1 V _{PK} , f = 400 MHz	
			100	—		V _{IN} = 0.1 V _{PK} , f = 900 MHz	
		_	101			V _{IN} = 0.1 V _{PK} , f = 1800 MHz	
		—	105	_		V _{IN} = 0.1 V _{PK} , f = 2400 MHz	

TABLE 1-2: AC ELECTRICAL SPECIFICATIONS

Note 1: These parameters were characterized using the circuit in Figure 1-6. In Figures 2-40 and 2-41, there is an IMD tone at DC, a residual tone at 1 kHz and other IMD tones and clock tones. IMD is Referred to Input (RTI).

2: High gains behave differently; see Section 4.3.3 "Offset at Power-Up".

3: t_{STL and} t_{ODR} include some uncertainty due to clock edge timing.

TABLE 1-3: TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, all limits are specified for: V_{DD} = +2.2V to +5.5V, V_{SS} = GND.									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Temperature Ranges									
Specified Temperature Range	T _A	-40	—	+125	°C				
Operating Temperature Range	T _A	-40	—	+125	°C	Note 1			
Storage Temperature Range	T _A	-65	—	+150	°C				
Thermal Package Resistances									
Thermal Resistance, 5LD-SC70	θ_{JA}	—	209	—	°C/W				
Thermal Resistance, 5LD-SOT-23	θ_{JA}	—	201	—	°C/W				
Thermal Resistance, 8L-2x3 TDFN	θ_{JA}	—	53	—	°C/W				
Thermal Resistance, 8L-MSOP	θ_{JA}	—	211	—	°C/W				
Thermal Resistance, 14L-TSSOP	θ_{JA}	_	100	_	°C/W				

Note 1: Operation must not cause T_J to exceed Maximum Junction Temperature specification (+150°C).

1.3 Timing Diagrams

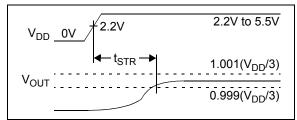


FIGURE 1-1: Amplifier Start-Up.

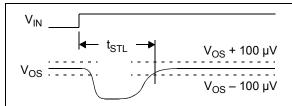
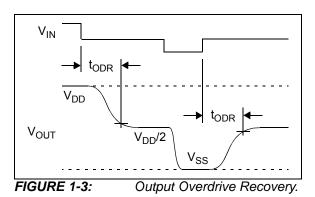


FIGURE 1-2: Offset Correction Settling Time.



1.4 Test Circuits

The circuits used for most DC and AC tests are shown in Figures 1-4 and 1-5. Lay the bypass capacitors out as discussed in **Section 4.3.10** "**Supply Bypassing and Filtering**". R_N is equal to the parallel combination of R_F and R_G to minimize bias current effects.

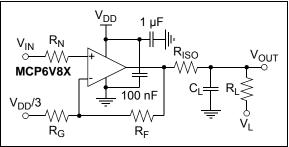


FIGURE 1-4: AC and DC Test Circuit for Most Non-Inverting Gain Conditions.

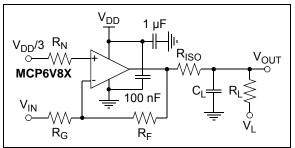


FIGURE 1-5: AC and DC Test Circuit for Most Inverting Gain Conditions.

The circuit in Figure 1-6 tests the input's dynamic behavior (i.e., IMD, t_{STR} , t_{STL} and t_{ODR}). The potentiometer balances the resistor network (V_{OUT} should equal V_{REF} at DC). The op amp's common-mode input voltage is V_{CM} = V_{IN}/2. The error at the input (V_{ERR}) appears at V_{OUT} with a noise gain of 10 V/V.

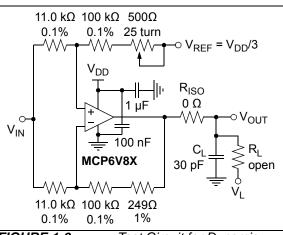


FIGURE 1-6: Test Circuit for Dynamic Input Behavior.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}$ C, $V_{DD} = +2.2$ V to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

2.1 **DC Input Precision**

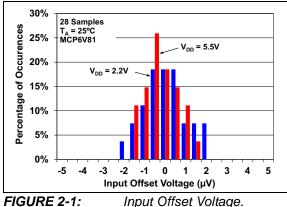
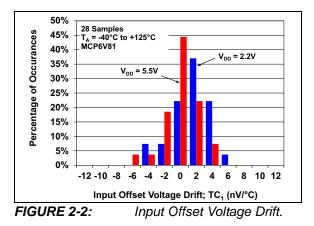


FIGURE 2-1:



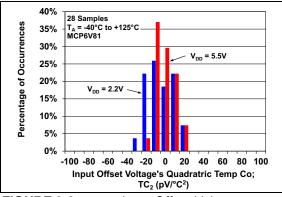


FIGURE 2-3: Input Offset Voltage Quadratic Temperature Coefficient.

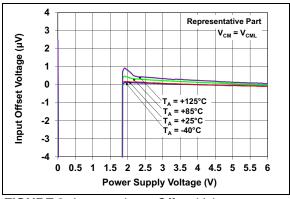


FIGURE 2-4: Input Offset Voltage vs. Power Supply Voltage with $V_{CM} = V_{CML}$.

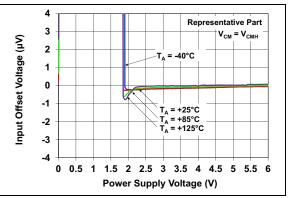
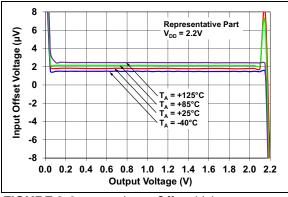
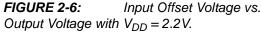


FIGURE 2-5: Input Offset Voltage vs. Power Supply Voltage with $V_{CM} = V_{CMH}$.





Note: Unless otherwise indicated, $T_A = +25$ °C, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

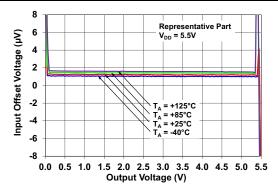


FIGURE 2-7: Input Offset Voltage vs. Output Voltage with $V_{DD} = 5.5V$.

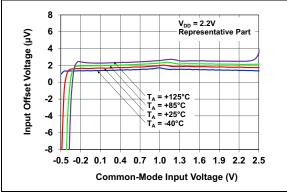


FIGURE 2-8: Input Offset Voltage vs. Common-Mode Voltage with $V_{DD} = 2.2V$.

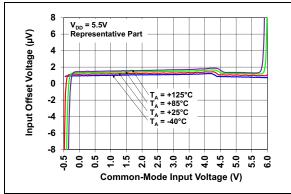


FIGURE 2-9: Input Offset Voltage vs. Common-Mode Voltage with $V_{DD} = 5.5V$.

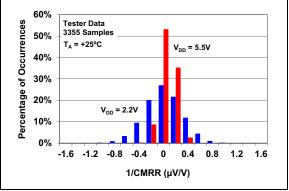


FIGURE 2-10: Common-Mode Rejection Ratio.

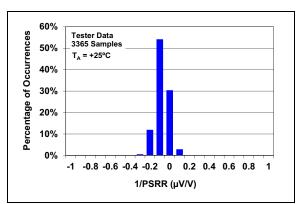


FIGURE 2-11: Power Supply Rejection Ratio.

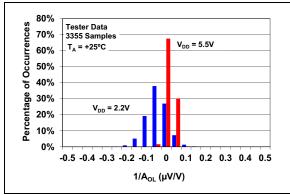


FIGURE 2-12: DC Open-Loop Gain.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

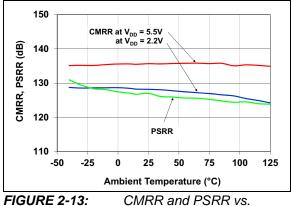


FIGURE 2-13: CMRR and Ambient Temperature.

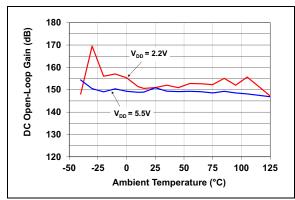


FIGURE 2-14: DC Open-Loop Gain vs. Ambient Temperature.

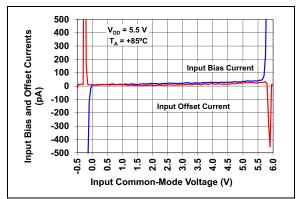


FIGURE 2-15: Input Bias and Offset Currents vs. Common-Mode Input Voltage with $T_A = +85$ °C.

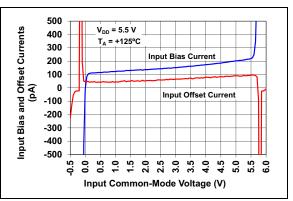


FIGURE 2-16: Input Bias and Offset Currents vs. Common-Mode Input Voltage with $T_A = +125$ °C.

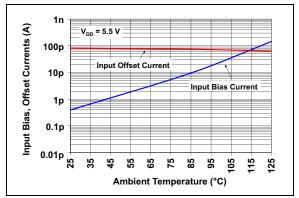


FIGURE 2-17: Input Bias and Offset Currents vs. Ambient Temperature with $V_{DD} = 5.5V$.

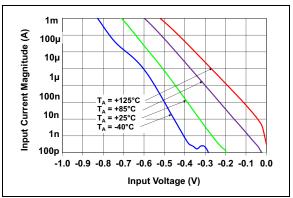


FIGURE 2-18: Input Bias Current vs. Input Voltage (Below V_{SS}).

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

2.2 Other DC Voltages and Currents

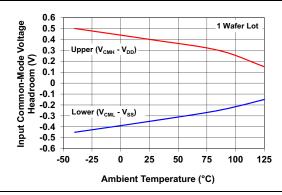


FIGURE 2-19: Input Common-Mode Voltage Headroom (Range) vs. Ambient Temperature.

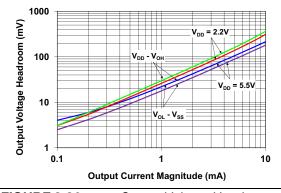


FIGURE 2-20: Output Voltage Headroom vs. Output Current.

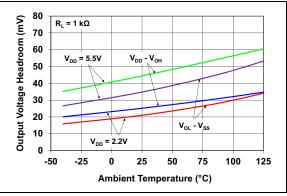


FIGURE 2-21: Output Voltage Headroom vs. Ambient Temperature.

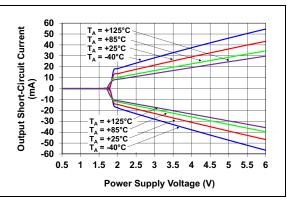


FIGURE 2-22: Output Short-Circuit Current vs. Power Supply Voltage.

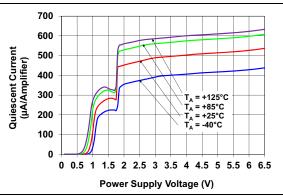
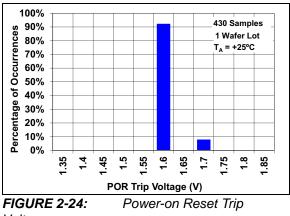


FIGURE 2-23: Supply Current vs. Power Supply Voltage.



Voltage.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

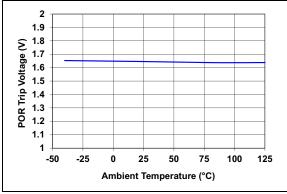
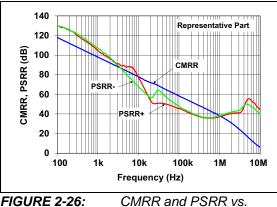


FIGURE 2-25: Power-on Reset Voltage vs. Ambient Temperature.

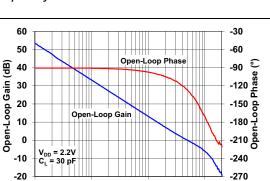
Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

2.3 Frequency Response





10k



1M

f (Hz)

10M

FIGURE 2-27: Open-Loop Gain vs. Frequency with $V_{DD} = 2.2V$.

100k

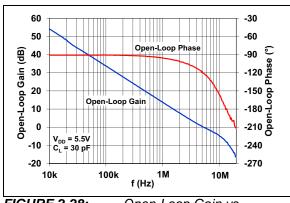


FIGURE 2-28: Open-Loop Gain vs. Frequency with $V_{DD} = 5.5V$.

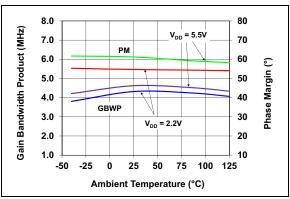


FIGURE 2-29: Gain Bandwidth Product and Phase Margin vs. Ambient Temperature.

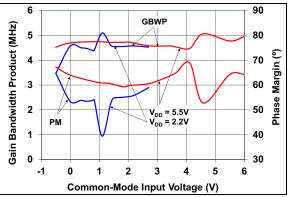


FIGURE 2-30: Gain Bandwidth Product and Phase Margin vs. Common-Mode Input Voltage.

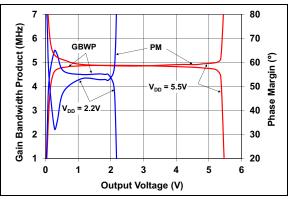


FIGURE 2-31: Gain Bandwidth Product and Phase Margin vs. Output Voltage.

Note: Unless otherwise indicated, $T_A = +25$ °C, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

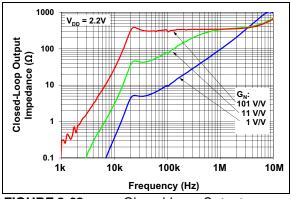


FIGURE 2-32: Closed-Loop Output Impedance vs. Frequency with $V_{DD} = 2.2V$.

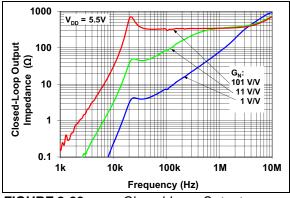


FIGURE 2-33: Closed-Loop Output Impedance vs. Frequency with $V_{DD} = 5.5V$.

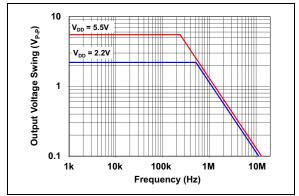
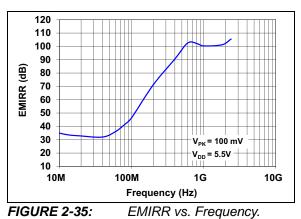


FIGURE 2-34: Maximum Output Voltage Swing vs. Frequency.



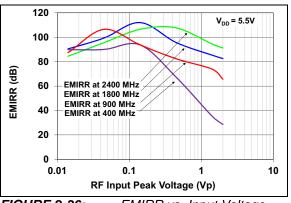
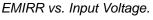


FIGURE 2-36: EMIRR vs.



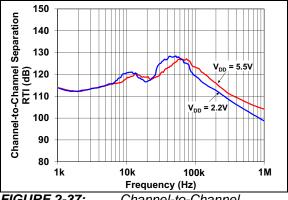


FIGURE 2-37: Channel-to-Channel Separation vs. Frequency.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

2.4 Input Noise and Distortion

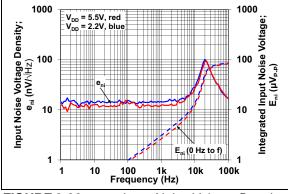


FIGURE 2-38: Input Noise Voltage Density and Integrated Input Noise Voltage vs. Frequency.

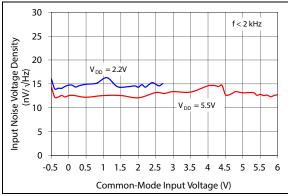


FIGURE 2-39: Input Noise Voltage Density vs. Input Common-Mode Voltage.

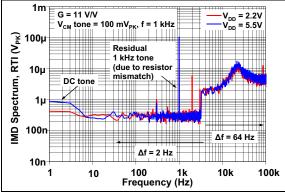


FIGURE 2-40: Intermodulation Distortion vs. Frequency with V_{CM} Disturbance (see Figure 1-6).

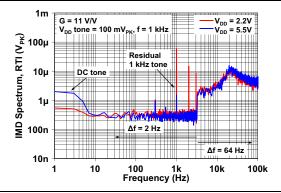


FIGURE 2-41: Intermodulation Distortion vs. Frequency with V_{DD} Disturbance (see Figure 1-6).

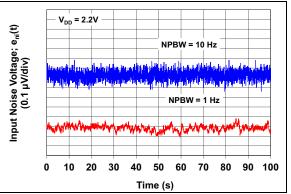


FIGURE 2-42: Input Noise vs. Time with 1 Hz and 10 Hz Filters and $V_{DD} = 2.2V$.

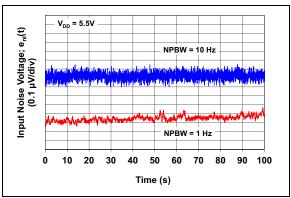
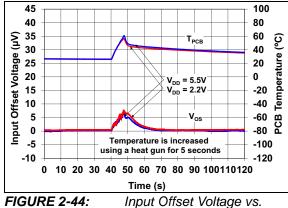
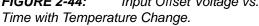


FIGURE 2-43: Input Noise vs. Time with 1 Hz and 10 Hz Filters and $V_{DD} = 5.5V$.

Note: Unless otherwise indicated, $T_A = +25$ °C, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

2.5 Time Response





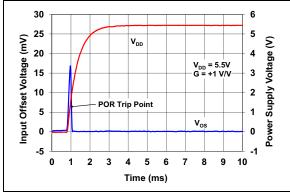


FIGURE 2-45: Input Offset Voltage vs. Time at Power-Up.

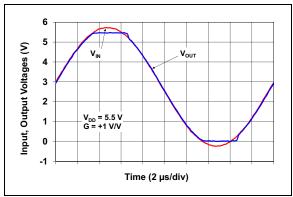


FIGURE 2-46: The MCP6V81/1U/2/4 Family Shows No Input Phase Reversal with Overdrive.

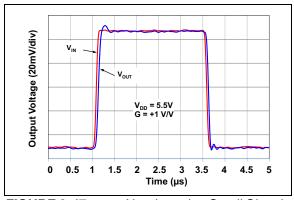


FIGURE 2-47: Non-Inverting Small Signal Step Response.

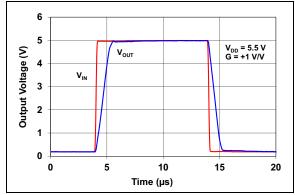


FIGURE 2-48: Non-Inverting Large Signal Step Response.

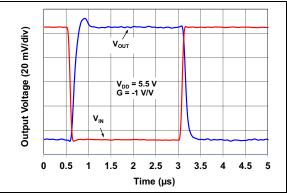


FIGURE 2-49: Inverting Small Signal Step Response.

Note: Unless otherwise indicated, $T_A = +25$ °C, $V_{DD} = +2.2V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 30 \text{ pF}$.

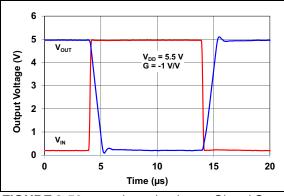


FIGURE 2-50: Inverting Large Signal Step Response.

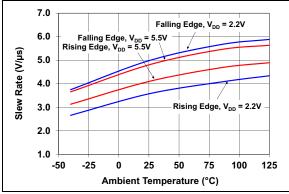


FIGURE 2-51: Slew Rate vs. Ambient Temperature.

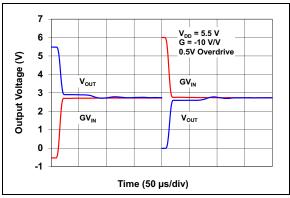


FIGURE 2-52: Output Overdrive Recovery vs. Time with G = -10 V/V.

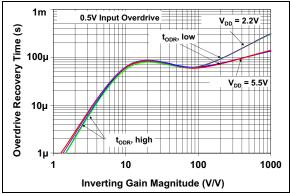


FIGURE 2-53: Output Overdrive Recovery Time vs. Inverting Gain.

3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

MCP6V81	MCP6V81U	MCP	6V82	MCP6V84		
SOT-23	SOT-23, SC70	2X3 TDFN	MSOP	TSSOP	Symbol	Description
1	4	1	1	1	V _{OUT}	Output
4	3	2	2	2	V _{IN} -	Inverting Input
3	1	3	3	3	V _{IN} +	Non-Inverting Input
5	5	8	8	4	V _{DD}	Positive Power Supply
—	—	5	5	5	V _{INB} +	Non-inverting Input (Op Amp B)
—	—	6	6	6	V _{INB} -	Inverting Input (Op Amp B)
_	—	7	7	7	V _{OUTB}	Output (Op Amp B)
_	—	_	—	8	V _{OUTC}	Output (Op Amp C)
—	—	_	—	9	V _{INC} -	Inverting Input (Op Amp C)
_	—	_	—	10	V _{INC} +	Non-inverting Input (Op Amp C)
2	2	4	4	11	V _{SS}	Negative Power Supply
—	—	_	—	12	V _{IND} +	Non-inverting Input (Op Amp D)
	—	_		13	V _{IND} -	Inverting Input (Op Amp D)
_	_	_		14	V _{OUTD}	Output (Op Amp D)
_	—	9	—	—	EP	Exposed Thermal Pad (EP); must be connected to V _{SS}

TABLE 3-1: PIN FUNCTION TABLE

3.1 Analog Outputs (V_{OUT}, V_{OUTA}, V_{OUTB}, V_{OUTC}, V_{OUTD})

The analog output pins are low-impedance voltage sources.

3.2 Analog Inputs (V_{IN} -, V_{IN} +, V_{INB} +, V_{INB} -, V_{INC} -, V_{INC} +, V_{IND} +, V_{IND} -)

The non-inverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

3.3 Power Supply Pins (V_{DD}, V_{SS})

The positive power supply (V_{DD}) is 2.2V to 5.5V higher than the negative power supply (V_{SS}). For normal operation, the other pins are between V_{SS} and V_{DD}.

Typically, these parts are used in a single (positive) supply configuration. In this case, V_{SS} is connected to ground and V_{DD} is connected to the supply. V_{DD} will need bypass capacitors.

3.4 Exposed Thermal Pad (EP)

There is an internal connection between the exposed thermal pad (EP) and the V_{SS} pin; they must be connected to the same potential on the printed circuit board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance (θ_{JA}).

NOTES:

4.0 APPLICATIONS

The MCP6V81/1U/2/4 family of zero-drift op amps is manufactured using Microchip's state-of-the-art CMOS process. It is designed for precision applications with requirements for small packages and low power. Its low supply voltage and low quiescent current make the MCP6V81/1U/2/4 devices ideal for battery-powered applications.

4.1 Overview of Zero-Drift Operation

Figure 4-1 shows a simplified diagram of the MCP6V81/1U/2/4 zero-drift op amp. This diagram will be used to explain how slow voltage errors are reduced in this architecture (much better V_{OS} , $\Delta V_{OS}/\Delta T_A$ (TC₁), CMRR, PSRR, A_{OL} and 1/f noise).

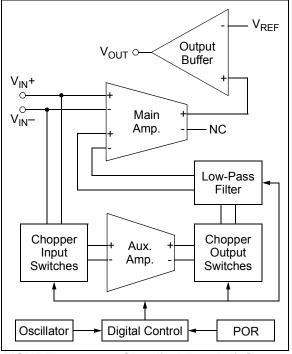


FIGURE 4-1: Simplified Zero-Drift Op Amp Functional Diagram.

4.1.1 BUILDING BLOCKS

The main amplifier is designed for high gain and bandwidth, with a differential topology. Its main input pair (+ and - pins at the top left) is used for the higher frequency portion of the input signal. Its auxiliary input pair (+ and - pins at the bottom left) is used for the low-frequency portion of the input signal and corrects the op amp's input offset voltage. Both inputs are added together internally.

The auxiliary amplifier, chopper input switches and chopper output switches provide a high DC gain to the input signal. DC errors are modulated to higher frequencies, while white noise is modulated to a low frequency. The low-pass filter reduces high-frequency content, including harmonics of the chopping clock.

The output buffer drives external loads at the V_{OUT} pin (V_{\text{REF}} is an internal reference voltage).

The oscillator runs at f_{OSC1} = 200 kHz. Its output is divided by two, to produce the chopping clock rate of f_{CHOP} = 100 kHz.

The internal Power-on Reset (POR) starts the part in a known good state, protecting against power supply brown-outs.

The digital control block controls switching and POR events.

4.1.2 CHOPPING ACTION

Figure 4-2 shows the amplifier connections for the first phase of the chopping clock and Figure 4-3 shows the connections for the second phase. Its slow voltage errors alternate in polarity, making the average error small.

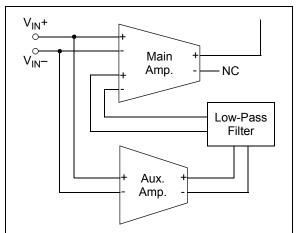


FIGURE 4-2: First Chopping Clock Phase; Equivalent Amplifier Diagram.

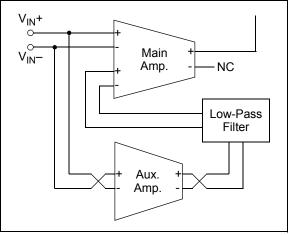


FIGURE 4-3: Second Chopping Clock Phase; Equivalent Amplifier Diagram.

4.1.3 INTERMODULATION DISTORTION (IMD)

These op amps will show intermodulation distortion (IMD) products when an AC signal is present.

The signal and clock can be decomposed into sine wave tones (Fourier series components). These tones interact with the zero-drift circuitry's nonlinear response to produce IMD tones at sum and difference frequencies. Each of the square wave clock's harmonics has a series of IMD tones centered on it (see Figures 2-40 and 2-41).

4.2 Other Functional Blocks

4.2.1 RAIL-TO-RAIL INPUTS

The input stage of the MCP6V81/1U/2/4 op amps uses two differential CMOS input stages in parallel. One operates at low common-mode input voltage (V_{CM}, which is approximately equal to V_{IN}+ and V_{IN}- in normal operation), and the other operates at high V_{CM}. With this topology, the input operates with V_{CM} up to V_{DD} + 0.3V and down to V_{SS} - 0.2V, at +25°C (see Figure 2-19). The input offset voltage (V_{OS}) is measured at V_{CM} = V_{SS} - 0.2V and V_{DD} + 0.3V to ensure proper operation.

4.2.1.1 Phase Reversal

The input devices are designed to not exhibit phase inversion when the input pins exceed the supply voltages. Figure 2-46 shows an input voltage exceeding both supplies with no phase inversion.

4.2.1.2 Input Voltage Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see Section 1.1 "Absolute Maximum Ratings †"). This requirement is independent of the input current limits discussed later on.

The ESD protection on the inputs can be depicted as shown in Figure 4-4. This structure was chosen to protect the input transistors against many (but not all) overvoltage conditions and to minimize input bias current (I_B).

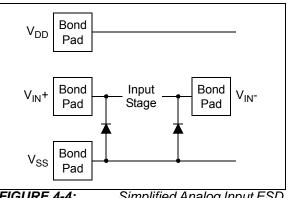


FIGURE 4-4: Simplified Analog Input ESD Structures.

The input ESD diodes clamp the inputs when they try to go more than one diode drop below V_{SS} . They also clamp any voltages well above V_{DD} ; their breakdown voltage is high enough to allow normal operation but not low enough to protect against slow overvoltage (beyond V_{DD}) events. Very fast ESD events (that meet the specification) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs; Figure 4-5 shows one approach to protecting these inputs. D_1 and D_2 may be small signal silicon diodes, Schottky diodes for lower clamping voltages or diode-connected FETs for low leakage.

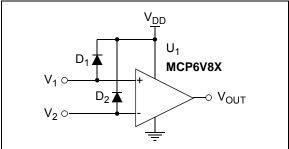


FIGURE 4-5: Protecting the Analog Inputs Against High Voltages.

4.2.1.3 Input Current Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents into the input pins (see **Section 1.1 "Absolute Maximum Ratings †**"). This requirement is independent of the voltage limits discussed previously.

Figure 4-6 shows one approach to protecting these inputs. The R_1 and R_2 resistors limit the possible current in or out of the input pins (and into D_1 and D_2). The diode currents will dump onto V_{DD} .

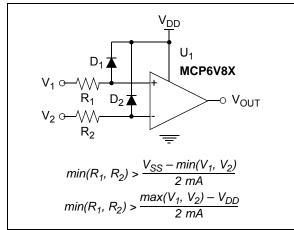


FIGURE 4-6: Protecting the Analog Inputs Against High Currents.

It is also possible to connect the diodes to the left of the R₁ and R₂ resistors. In this case, the currents through the D₁ and D₂ diodes need to be limited by some other mechanism. The resistors then serve as in-rush current limiters; the DC current into the input pins (V_{IN}+ and V_{IN}-) should be very small.

A significant amount of current can flow out of the inputs (through the ESD diodes) when the common-mode input voltage (V_{CM}) is below ground (V_{SS}) (see Figure 2-18).

4.2.2 RAIL-TO-RAIL OUTPUT

The output voltage range of the MCP6V81/1U/2/4 zero-drift op amps is V_{DD} – 5 mV (typical) and V_{SS} + 5 mV (typical) when R_L = 10 k Ω is connected to V_{DD}/2 and V_{DD} = 5.5V. Refer to Figures 2-20 and 2-21 for more information.

This op amp is designed to drive light loads; use another amplifier to buffer the output from heavy loads.

4.3 Application Tips

4.3.1 INPUT OFFSET VOLTAGE OVER TEMPERATURE

Table 1-1 gives both the linear and quadratic temperature coefficients (TC_1 and TC_2) of input offset voltage. The input offset voltage, at any temperature in the specified range, can be calculated as follows:

EQUATION 4-1:

$$\begin{split} V_{OS}(T_A) &= V_{OS} + TC_1 \varDelta T + TC_2 \varDelta T^2 \\ \text{Where:} \\ \Delta T &= T_A - 25^\circ \text{C} \\ V_{OS}(T_A) &= \text{Input offset voltage at } T_A \\ V_{OS} &= \text{Input offset voltage at } +25^\circ \text{C} \\ TC_1 &= \text{Linear temperature coefficient} \\ TC_2 &= \text{Quadratic temperature coefficient} \end{split}$$

4.3.2 DC GAIN PLOTS

Figures 2-10 to 2-12 are histograms of the reciprocals (in units of μ V/V) of CMRR, PSRR and A_{OL}, respectively. They represent the change in input offset voltage (V_{OS}) with a change in common-mode input voltage (V_{CM}), power supply voltage (V_{DD}) and output voltage (V_{OUT}). The histograms are based on data taken with the production test equipment and the results reflect the trade-off between accuracy and test time. The actual performance of the devices is typically higher than shown in Figures 2-10 to 2-12.

The 1/A_{OL} histogram is centered near 0 μ V/V because the measurements are dominated by the op amp's input noise. The negative values shown represent noise and tester limitations, *not* unstable behavior. Production tests make multiple V_{OS} measurements, which validates an op amp's stability; an unstable part would show greater V_{OS} variability or the output would stick at one of the supply rails.

4.3.3 OFFSET AT POWER-UP

When these parts power up, the input offset (V_{OS}) starts at its uncorrected value (usually less than ± 5 mV). Circuits with high DC gain can cause the output to reach one of the two rails. In this case, the time to a valid output is delayed by an output overdrive time (like t_{ODR}) in addition to the start-up time (like t_{STR}).

It can be simple to avoid this extra start-up time. Reducing the gain is one method. Adding a capacitor across the feedback resistor (R_F) is another method.

4.3.4 SOURCE RESISTANCES

The input bias currents have two significant components: switching glitches that dominate at room temperature and below, and input ESD diode leakage currents that dominate at +85°C and above.

Make the resistances seen by the inputs small and equal. This minimizes the output offset caused by the input bias currents.

The inputs should see a resistance on the order of 10Ω to 1 kΩ at high frequencies (i.e., above 1 MHz). This helps minimize the impact of switching glitches, which are very fast, on overall performance. In some cases, it may be necessary to add resistors in series with the inputs to achieve this improvement in performance.

Small input resistances may be needed for high gains. Without them, parasitic capacitances might cause positive feedback and instability.

4.3.5 SOURCE CAPACITANCE

The capacitances seen by the two inputs should be small. Large input capacitances and source resistances, together with high gain, can lead to positive feedback and instability.

4.3.6 CAPACITIVE LOADS

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. These zero-drift op amps have a different output impedance than most op amps, due to their unique topology.

When driving a capacitive load with these op amps, a series resistor at the output (R_{ISO} in Figure 4-7) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.

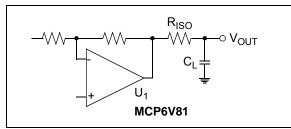


FIGURE 4-7: Output Resistor, RISO, Stabilizes Capacitive Loads.

Figure 4-8 gives recommended R_{ISO} values for different capacitive loads and gains. The x-axis is the load capacitance (C_1). The y-axis is the resistance (R_{ISO}).

G_N is the circuit's noise gain. For non-inverting gains, G_N and the Signal Gain are equal. For inverting gains, G_N is 1+|Signal Gain| (e.g., -1 V/V gives G_N = +2 V/V).

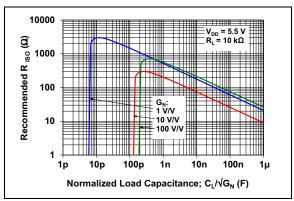


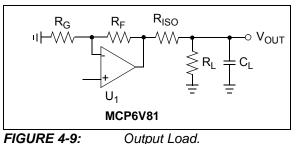
FIGURE 4-8: Recommended RISO values for Capacitive Loads.

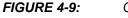
After selecting RISO for your circuit, double check the resulting frequency response peaking and step response overshoot. Modify the RISO value until the response is reasonable. Bench evaluation is helpful.

4.3.7 STABILIZING OUTPUT LOADS

This family of zero-drift op amps has an output impedance that has a double zero when the gain is low (see Figures 2-32 and 2-33). This can cause a large phase shift in feedback networks that have lowimpedance near the part's bandwidth. This large phase shift can cause stability problems.

Figure 4-9 shows that the load on the output is $(R_L + R_{ISO})||(R_F + R_G)$, where R_{ISO} is before the load (like Figure 4-7). This load needs to be large enough to maintain stability; it should be at least 10 k Ω .





4.3.8 GAIN PEAKING

Figure 4-10 shows an op amp circuit that represents non-inverting amplifiers (V_M is a DC voltage and V_P is the input) or inverting amplifiers (V_P is a DC voltage and V_M is the input). The C_N and C_G capacitances represent the total capacitance at the input pins; they include the op amp's common-mode input capacitance (C_{CM}), board parasitic capacitance and any capacitor placed in parallel. The C_{FP} capacitance represents the parasitic capacitance coupling the output and non-inverting input pins.

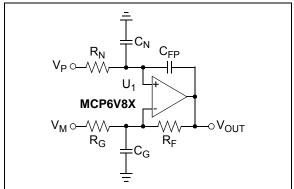


FIGURE 4-10: A Capacitance.

Amplifier with Parasitic

 C_G acts in parallel with R_G (except for a gain of +1 V/V), which causes an increase in gain at high frequencies. C_G also reduces the phase margin of the feedback loop, which becomes less stable. This effect can be reduced by reducing either C_G or $R_F||R_G$.

 C_N and R_N form a low-pass filter that affects the signal at V_P . This filter has a single real pole at $1/(2\pi R_N C_N)$.

The largest value of R_F that should be used depends on noise gain (see G_N in Section 4.3.6 "Capacitive Loads"), C_G and the open-loop gain's phase shift. An approximate limit for R_F is:

EQUATION 4-2:

$$R_F \le 10 \, k \Omega \times \frac{3.5 \, pF}{C_G} \times G_N^2$$

Some applications may modify these values to reduce either output loading or gain peaking (step-response overshoot).

At high gains, $R_{\rm N}$ needs to be small in order to prevent positive feedback and oscillations. Large $C_{\rm N}$ values can also help.

4.3.9 REDUCING UNDESIRED NOISE AND SIGNALS

Reduce undesired noise and signals with:

- · Low-bandwidth signal filters:
 - Minimize random analog noise
 - Reduce interfering signals
- · Good PCB layout techniques:
 - Minimize crosstalk
 - Minimize parasitic capacitances and inductances that interact with fast-switching edges
- Good power supply design:
 - Isolation from other parts
 - Filtering of interference on supply line(s)

4.3.10 SUPPLY BYPASSING AND FILTERING

With this family of operational amplifiers, the power supply pin (V_{DD} for single supply) should have a local bypass capacitor (i.e., $0.01 \ \mu F$ to $0.1 \ \mu F$) within 2 mm of the pin for good high-frequency performance.

These parts also need a bulk capacitor (i.e., $1 \ \mu F$ or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other low-noise analog parts.

In some cases, high-frequency power supply noise (e.g., switched mode power supplies) may cause undue intermodulation distortion with a DC offset shift; this noise needs to be filtered. Adding a small resistor into the supply connection can be helpful.

4.3.11 PCB DESIGN FOR DC PRECISION

In order to achieve DC precision on the order of $\pm 1 \mu$ V, many physical errors need to be minimized. The design of the printed circuit board (PCB), the wiring and the thermal environment have a strong impact on the precision achieved. A poor PCB design can easily be more than 100 times worse than the MCP6V81/1U/2/4 op amps' minimum and maximum specifications.

4.3.11.1 PCB Layout

Any time two dissimilar metals are joined together, a temperature-dependent voltage appears across the junction (the Seebeck or thermojunction effect). This effect is used in thermocouples to measure temperature. The following are examples of thermojunctions on a PCB:

- Components (resistors, op amps, ...) soldered to a copper pad
- · Wires mechanically attached to the PCB
- Jumpers
- Solder joints
- PCB vias

Typical thermojunctions have temperature-to-voltage conversion coefficients of 1 to 100 $\mu\text{V}/^{\circ}\text{C}$ (sometimes higher).

Microchip's AN1258 "*Op Amp Precision Design: PCB Layout Techniques*" (DS01258) contains in-depth information on PCB layout techniques that minimize thermojunction effects. It also discusses other effects, such as crosstalk, impedances, mechanical stresses and humidity.

4.3.11.2 Crosstalk

DC crosstalk causes offsets that appear as a larger input offset voltage. Common causes include:

- Common-mode noise (remote sensors)
- Ground loops (current return paths)
- Power supply coupling

Interference from the mains (usually 50 Hz or 60 Hz) and other AC sources can also affect the DC performance. Nonlinear distortion can convert these signals to multiple tones, including a DC shift in voltage. When the signal is sampled by an ADC, these AC signals can also be aliased to DC, causing an apparent shift in offset.

To reduce interference:

- Keep traces and wires as short as possible
- Use shielding
- Use ground plane (at least a star ground)
- Place the input signal source near the DUT
- Use good PCB layout techniques
- Use a separate power supply filter (bypass capacitors) for these zero-drift op amps

4.3.11.3 Miscellaneous Effects

Keep the resistances seen by the input pins as small and as near to equal as possible to minimize bias current-related offsets.

Make the (trace) capacitances seen by the input pins small and equal. This is helpful in minimizing switching glitch-induced offset voltages.

Bending a coax cable with a radius that is too small causes a small voltage drop to appear on the center conductor (the triboelectric effect). Make sure the bending radius is large enough to keep the conductors and insulation in full contact.

Mechanical stresses can make some capacitor types (such as some ceramics) output small voltages. Use more appropriate capacitor types in the signal path and minimize mechanical stresses and vibration.

Humidity can cause electrochemical potential voltages to appear in a circuit. Proper PCB cleaning helps, as does the use of encapsulants.

4.4 Typical Applications

4.4.1 WHEATSTONE BRIDGE

Many sensors are configured as Wheatstone bridges. Strain gauges and pressure sensors are two common examples. These signals can be small and the common-mode noise large. Amplifier designs with high differential gain are desirable.

Figure 4-11 shows how to interface to a Wheatstone bridge with a minimum of components. Because the circuit is not symmetric, the ADC input is single-ended and there is a minimum of filtering; the CMRR is good enough for moderate common-mode noise.

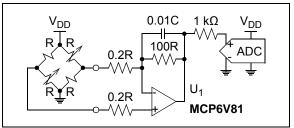
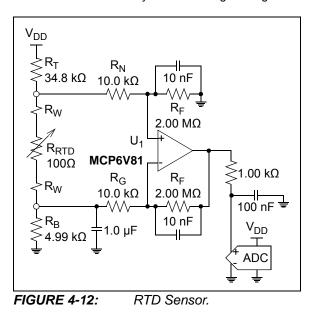


FIGURE 4-11: Simple Design.

4.4.2 RTD SENSOR

The ratiometric circuit in Figure 4-12 conditions a two-wire RTD for applications with a limited temperature range. U_1 acts as a difference amplifier with a low-frequency pole. The sensor's wiring resistance (R_W) is corrected in firmware. Failure (open) of the RTD is detected by an out-of-range voltage.



4.4.3 OFFSET VOLTAGE CORRECTION

Figure 4-13 shows MCP6V81 (U₂) correcting the input offset voltage of another op amp (U₁). R₂ and C₂ integrate the offset error seen at U₁'s input. The integration needs to be slow enough to be stable (with the feedback provided by R₁ and R₃). R₄ and R₅ attenuate the integrator's output. This shifts the integrator pole down in frequency.

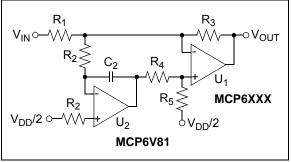


FIGURE 4-13: Offset Correction.

4.4.4 PRECISION COMPARATOR

Use high gain before a comparator to improve the latter's performance. Do not use MCP6V81/1U/2/4 as a comparator by itself; the V_{OS} correction circuitry does not operate properly without a feedback loop.

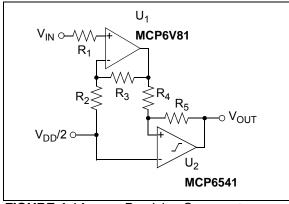


FIGURE 4-14:

Precision Comparator.

NOTES:

5.0 DESIGN AIDS

Microchip provides the basic design aids needed for the MCP6V81/1U/2/4 family of op amps.

5.1 FilterLab[®] Software

Microchip's FilterLab[®] software is an innovative software tool that simplifies analog active filter (using op amps) design. Available at no cost from the Microchip web site at www.microchip.com/filterlab, the FilterLab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate actual filter performance.

5.2 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip web site at www.microchip.com/maps, MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, a customer can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for data sheets, purchase and sampling of Microchip parts.

5.3 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help customers achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site at www.microchip.com/analog tools.

Some boards that are especially useful are:

- MCP6V01 Thermocouple Auto-Zeroed Reference Design (P/N MCP6V01RD-TCPL)
- MCP6XXX Amplifier Evaluation Board 1 (P/N DS51667)
- MCP6XXX Amplifier Evaluation Board 2 (P/N DS51668)
- MCP6XXX Amplifier Evaluation Board 3 (P/N DS51673)
- MCP6XXX Amplifier Evaluation Board 4 (P/N DS51681)
- Active Filter Demo Board Kit (P/N DS51614)
- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board (P/N SOIC8EV)
- 14-Pin SOIC/TSSOP/DIP Evaluation Board (P/N SOIC14EV)

5.4 Application Notes

The following Microchip Application Notes are available on the Microchip web site at www.microchip. com/appnotes and are recommended as supplemental reference resources.

ADN003: "Select the Right Operational Amplifier for your Filtering Circuits" (DS21821)

AN722: "Operational Amplifier Topologies and DC Specifications" (DS00722)

AN723: "Operational Amplifier AC Specifications and Applications" (DS00723)

AN884: "Driving Capacitive Loads With Op Amps" (DS00884)

AN990: "Analog Sensor Conditioning Circuits – An Overview" (DS00990)

AN1177: "Op Amp Precision Design: DC Errors" (DS01177)

AN1228: "Op Amp Precision Design: Random Noise" (DS01228)

AN1258: "Op Amp Precision Design: PCB Layout Techniques" (DS01258)

AN1767: "Solutions for Radio Frequency Electromagnetic Interference in Amplifier Circuits" (DS01767A)

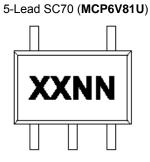
These Application Notes and others are listed in the design guide:

"Signal Chain Design Guide" (DS21825)

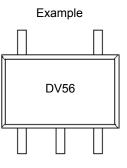
NOTES:

6.0 PACKAGING INFORMATION

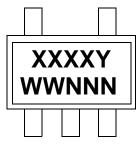
6.1 Package Marking Information



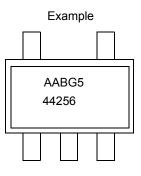
Device	Code
MCP6V81UT-E/LTY	DVNN



5-Lead SOT-23 (MCP6V81, MCP6V81U)



Device	Code
MCP6V81T-E/OT	AABGY
MCP6V81UT-E/OT	AABHY



8-Lead MSOP (MCP6V82)



8-Lead TDFN (MCP6V82)

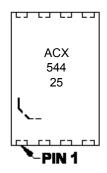


I	Device			
MCP6V8	ACT			
Note:	Applies to 8-Lead 2x3 TDFN.			

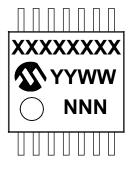
Example



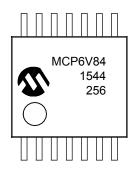
Example



14-Lead TSSOP (MCP6V84)



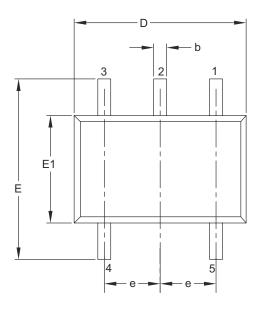
Example

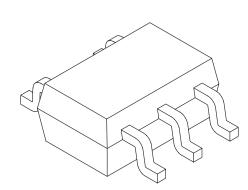


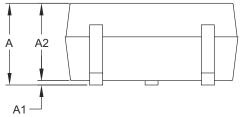
Legend	: XXX Y YY WW NNN @3 *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC [®] designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
Note:	be carrie	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

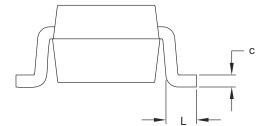
5-Lead Plastic Small Outine Transistor (LTY) [SC70]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









	Units			
Dimens	sion Limits	MIN	NOM	MAX
Number of Pins	Ν		5	
Pitch	е		0.65 BSC	
Overall Height	А	0.80	-	1.10
Molded Package Thickness	A2	0.80	-	1.00
Standoff	A1	0.00	-	0.10
Overall Width	E	1.80	2.10	2.40
Molded Package Width	E1	1.15	1.25	1.35
Overall Length	D	1.80	2.00	2.25
Foot Length	L	0.10	0.20	0.46
Lead Thickness	С	0.08	-	0.26
Lead Width	b	0.15	-	0.40

Notes:

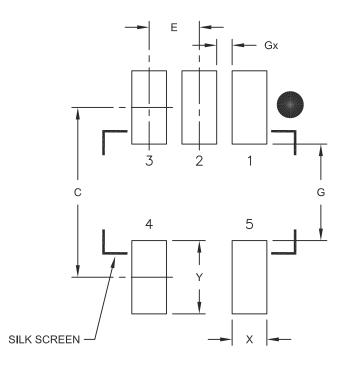
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-061B

5-Lead Plastic Small Outine Transistor (LTY) [SC70]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	Ν	ILLIMETER	S
Dimensior	Limits	MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	С		2.20	
Contact Pad Width	Х			0.45
Contact Pad Length	Y			0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

Notes:

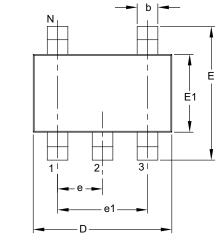
1. Dimensioning and tolerancing per ASME Y14.5M

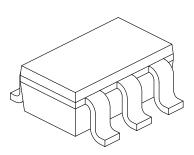
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2061A

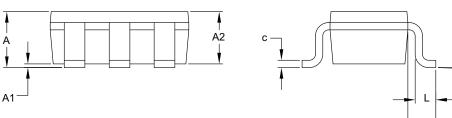
5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





L1



	Units	MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX
Number of Pins	N	5		
Lead Pitch	е	0.95 BSC		
Outside Lead Pitch	e1	1.90 BSC		
Overall Height	A	0.90	-	1.45
Molded Package Thickness	A2	0.89	-	1.30
Standoff	A1	0.00	-	0.15
Overall Width	E	2.20	-	3.20
Molded Package Width	E1	1.30	-	1.80
Overall Length	D	2.70	-	3.10
Foot Length	L	0.10	-	0.60
Footprint	L1	0.35	-	0.80
Foot Angle	ф	0°	-	30°
Lead Thickness	С	0.08	-	0.26
Lead Width	b	0.20	-	0.51

Notes:

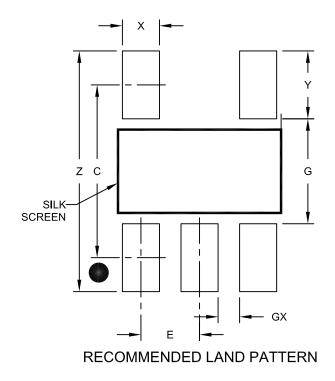
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	Units MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch E		0.95 BSC		
Contact Pad Spacing	С		2.80	
Contact Pad Width (X5)	Х			0.60
Contact Pad Length (X5)	Y			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Z			3.90

Notes:

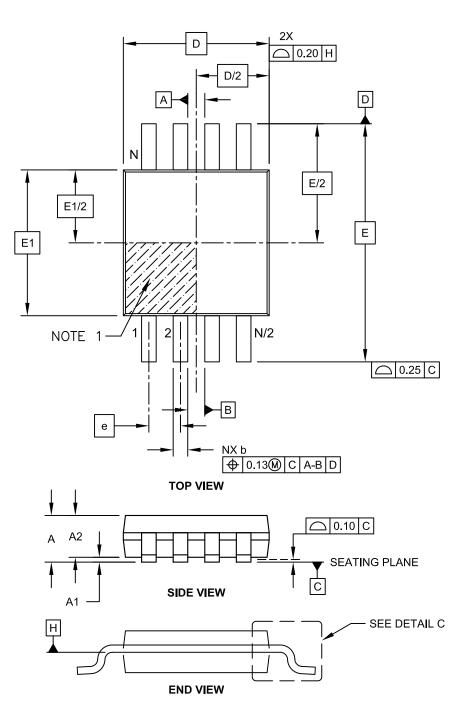
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

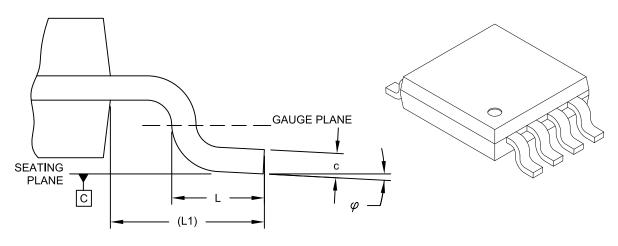
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-111C Sheet 1 of 2

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



DETAIL C

	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е	0.65 BSC		
Overall Height	A	-	-	1.10
Molded Package Thickness	A2	0.75	0.85	0.95
Standoff	A1	0.00	-	0.15
Overall Width	E	4.90 BSC		
Molded Package Width	E1	3.00 BSC		
Overall Length	D	3.00 BSC		
Foot Length	L	0.40	0.60	0.80
Footprint	L1	0.95 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.08	-	0.23
Lead Width	b	0.22	-	0.40

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or

- protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M.

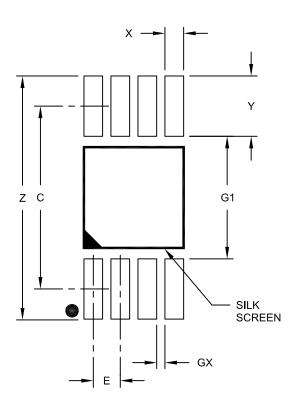
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units		MILLIMETERS		
Dimensior	Dimension Limits		NOM	MAX	
Contact Pitch	E	0.65 BSC			
Contact Pad Spacing	С		4.40		
Overall Width	Z			5.85	
Contact Pad Width (X8) X1				0.45	
Contact Pad Length (X8)	Y1			1.45	
Distance Between Pads	G1	2.95			
Distance Between Pads	GX	0.20			

Notes:

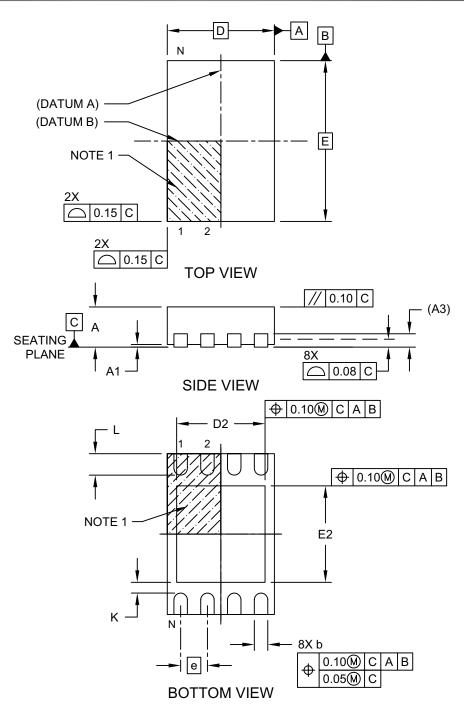
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

8-Lead Plastic Dual Flat, No Lead Package (MNY) – 2x3x0.75mm Body [TDFN]

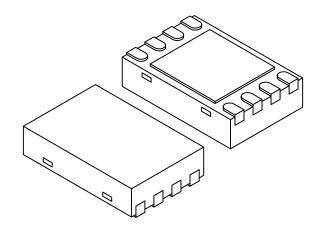
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-129-MNY Rev D Sheet 1 of 2

8-Lead Plastic Dual Flat, No Lead Package (MNY) – 2x3x0.75mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	Ν	8		
Pitch	е	0.50 BSC		
Overall Height	Α	0.70	0.75	0.80
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	2.00 BSC		
Overall Width	Е	3.00 BSC		
Exposed Pad Length	D2	1.45	-	1.65
Exposed Pad Width	E2	1.60	-	1.80
Contact Width	b	0.20	0.25	0.30
Contact Length	L	0.25	0.30	0.45
Contact-to-Exposed Pad	K	0.20		-

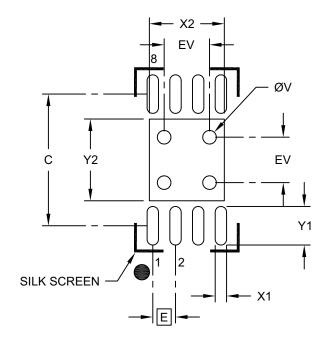
Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated
- 4. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129-MNY Rev D Sheet 2 of 2

8-Lead Plastic Dual Flat, No Lead Package (MNY) – 2x3x0.75mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E	0.50 BSC			
Optional Center Pad Width	X2			1.65	
Optional Center Pad Length	Y2			1.80	
Contact Pad Spacing	С		2.90		
Contact Pad Width (X8)	X1			0.25	
Contact Pad Length (X8)	Y1			0.85	
Thermal Via Diameter	V		0.30		
Thermal Via Pitch	EV		1.00		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

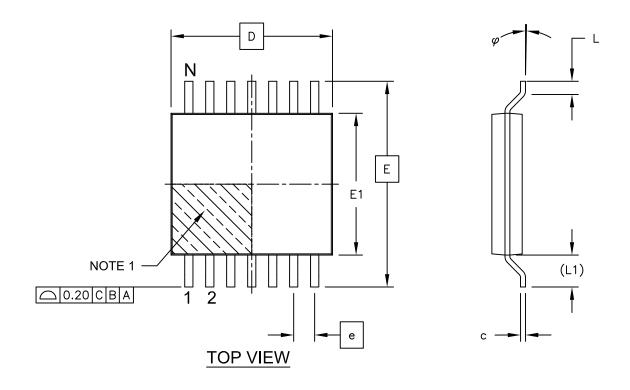
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

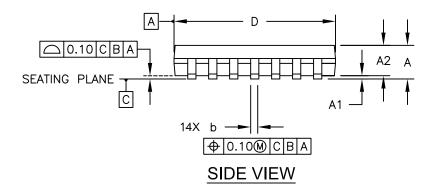
2. For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process

Microchip Technology Drawing No. C04-129-MNY Rev. A

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

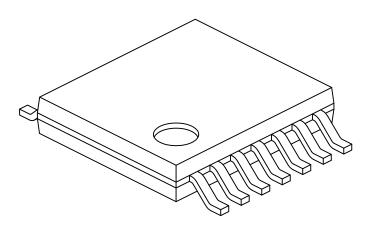




Microchip Technology Drawing C04-087C Sheet 1 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	nits MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N	14		
Pitch	е	0.65 BSC		
Overall Height	A	-	-	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	-	0.15
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30 4.40 4.5		4.50
Molded Package Length	D	4.90	5.00	5.10
Foot Length	L	0.45	0.60	0.75
Footprint	(L1)	1.00 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.09	-	0.20
Lead Width	b	0.19	-	0.30

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.

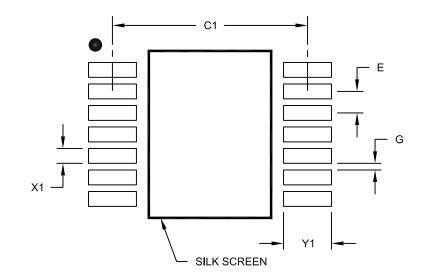
3. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimensior	Dimension Limits		NOM	MAX	
Contact Pitch	E	0.65 BSC			
Contact Pad Spacing	C1		5.90		
Contact Pad Width (X14)	X1			0.45	
Contact Pad Length (X14)	Y1			1.45	
Distance Between Pads	G	0.20			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

MCP6V81/1U/2/4

NOTES:

APPENDIX A: REVISION HISTORY

Revision B (March 2016)

The following is the list of modifications:

- 1. Added new devices to the family: MCP6V82 and MCP6V84, and related information throughout the document.
- 2. Added Figure 2-37.
- 3. Updated Table 3-1 in Section 3.0, Pin Descriptions.
- 4. Added markings and specification drawings for the new packages in Section 6.0, Packaging Information.
- 5. Updated the Product Identification System section with the new packages.
- 6. Corrected some typographical errors.

Revision A (June 2015)

Original Release of this Document.

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO. ΙΧΙ</u> (¹	¹⁾ <u>–× /××</u>	Exa	mples:	
 Device Tape and	l Reel Temperature Package Range	a)	MCP6V81T-E/OT:	Tape and Reel, Extended temperature, 5LD SOT-23 package
Device:	MCP6V81T: Single Op Amp (Tape and Reel) (SOT-23 only)	a)	MCP6V81UT-E/LTY:	Tape and Reel Extended temperature, 5LD SC70 package
	MCP6V81UT:Single Op Amp (Tape and Reel) (SC-70, SOT-23)MCP6V82:Dual Op Amp (MSOP, 2x3 TDFN)MCP6V82T:Dual Op Amp (Tape and Reel) (MSOP,	b)	MCP6V81UT-E/OT:	Tape and Reel, Extended temperature, 5LD SOT-23 package
	2x3 TDFN) MCP6V84: Quad Op Amp (TSSOP)	a)	MCP6V82-E/MS:	Extended temperature, 8LD MSOP package
	MCP6V84T: Quad Op Amp (Tape and Reel) (TSSOP)	b)	MCP6V82T-E/MS:	Tape and Reel, Extended temperature, 8LD MSOP package
Temperature Range: Package:	E = -40°C to +125°C (Extended) LTY* = Plastic Small Outline Transistor, SC-70, 5-lead	c)	MCP6V82T-E/MNY:	1 0
r donage.	OT = Plastic Small Outline Transistor, SOT-23, 5-lead MNY* = Plastic Dual Flat, No-Lead - 2×3×0.75 mm	a)	MCP6V84-E/ST:	Extended temperature, 14LD TSSOP package
	Body, 8-lead MS = Plastic Micro Small Outline, 8-lead ST = Plastic Thin Shrink Small Outline - 4.4 mm Body, 14-lead	b)	MCP6V84T-E/ST:	Tape and Reel, Extended temperature, 14LD TSSOP package
	*Y = Nickel palladium gold manufacturing designator. Only available on the SC70 package.	Note	catalog part nu	identifier only appears in the mber description. This identi-
			printed on the o your Microchip	ordering purposes and is not device package. Check with Sales Office for package the Tape and Reel option.

Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELoQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.

QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV = ISO/TS 16949=

Trademarks

The Microchip name and logo, the Microchip logo, AnyRate, dsPIC, FlashFlex, flexPWR, Heldo, JukeBlox, KeeLoq, KeeLoq logo, Kleer, LANCheck, LINK MD, MediaLB, MOST, MOST logo, MPLAB, OptoLyzer, PIC, PICSTART, PIC32 logo, RightTouch, SpyNIC, SST, SST Logo, SuperFlash and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

ClockWorks, The Embedded Control Solutions Company, ETHERSYNCH, Hyper Speed Control, HyperLight Load, IntelliMOS, mTouch, Precision Edge, and QUIET-WIRE are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Any Capacitor, AnyIn, AnyOut, BodyCom, chipKIT, chipKIT logo, CodeGuard, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, EtherGREEN, In-Circuit Serial Programming, ICSP, Inter-Chip Connectivity, JitterBlocker, KleerNet, KleerNet logo, MiWi, motorBench, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PureSilicon, RightTouch logo, REAL ICE, Ripple Blocker, Serial Quad I/O, SQI, SuperSwitcher, SuperSwitcher II, Total Endurance, TSHARC, USBCheck, VariSense, ViewSpan, WiperLock, Wireless DNA, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

Silicon Storage Technology is a registered trademark of Microchip Technology Inc. in other countries.

GestIC is a registered trademarks of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2016, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

ISBN: 978-1-5224-0352-4



Worldwide Sales and Service

AMERICAS

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: http://www.microchip.com/ support

Web Address: www.microchip.com

Atlanta Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Austin, TX Tel: 512-257-3370

Boston Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075

Cleveland Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

Dallas Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Novi, MI Tel: 248-848-4000

Houston, TX Tel: 281-894-5983

Indianapolis Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453

Los Angeles Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

New York, NY Tel: 631-435-6000

San Jose, CA Tel: 408-735-9110

Canada - Toronto Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office Suites 3707-14, 37th Floor Tower 6, The Gateway

Harbour City, Kowloon Hong Kong Tel: 852-2943-5100 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing Tel: 86-10-8569-7000 Fax: 86-10-8528-2104

China - Chengdu Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Chongqing Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

China - Dongguan Tel: 86-769-8702-9880

China - Hangzhou Tel: 86-571-8792-8115 Fax: 86-571-8792-8116

China - Hong Kong SAR Tel: 852-2943-5100 Fax: 852-2401-3431

China - Nanjing Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

China - Qingdao Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen Tel: 86-755-8864-2200 Fax: 86-755-8203-1760

China - Wuhan Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

ASIA/PACIFIC

China - Xiamen Tel: 86-592-2388138 Fax: 86-592-2388130

China - Zhuhai Tel: 86-756-3210040 Fax: 86-756-3210049

India - Bangalore Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

India - New Delhi Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune Tel: 91-20-3019-1500

Japan - Osaka Tel: 81-6-6152-7160 Fax: 81-6-6152-9310

Japan - Tokyo Tel: 81-3-6880- 3770 Fax: 81-3-6880-3771

Korea - Daegu Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu Tel: 886-3-5778-366 Fax: 886-3-5770-955

Taiwan - Kaohsiung Tel: 886-7-213-7828

Taiwan - Taipei Tel: 886-2-2508-8600 Fax: 886-2-2508-0102

Thailand - Bangkok Tel: 66-2-694-1351 Fax: 66-2-694-1350

EUROPE

Austria - Wels Tel: 43-7242-2244-39 Fax: 43-7242-2244-393

Denmark - Copenhagen Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Dusseldorf Tel: 49-2129-3766400

Germany - Munich Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Germany - Pforzheim Tel: 49-7231-424750

Italy - Milan Tel: 39-0331-742611 Fax: 39-0331-466781

Italy - Venice Tel: 39-049-7625286

Netherlands - Drunen Tel: 31-416-690399 Fax: 31-416-690340

Poland - Warsaw Tel: 48-22-3325737

Spain - Madrid Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

Sweden - Stockholm Tel: 46-8-5090-4654

UK - Wokingham Tel: 44-118-921-5800 Fax: 44-118-921-5820

01/27/15